



# STB185N10F3 STP185N10F3

N-channel 100 V, 4.0 mΩ, 120 A, D<sup>2</sup>PAK, TO-220  
STripFET™ Power MOSFET

Preliminary Data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB185N10F3	100 V	4.5 mΩ	120 A <sup>(1)</sup>
STP185N10F3	100 V	4.8 mΩ	120 A <sup>(1)</sup>

1. Value limited by wire bonding

- Ultra low on-resistance
- 100% avalanche tested

## Application

- Switching application
  - Automotive

## Description

This n-channel enhancement mode Power MOSFET is the latest refinement of STMicroelectronics unique “single feature size” strip-based process with less critical alignment steps and therefore a remarkable manufacturing reproducibility. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and low gate charge.

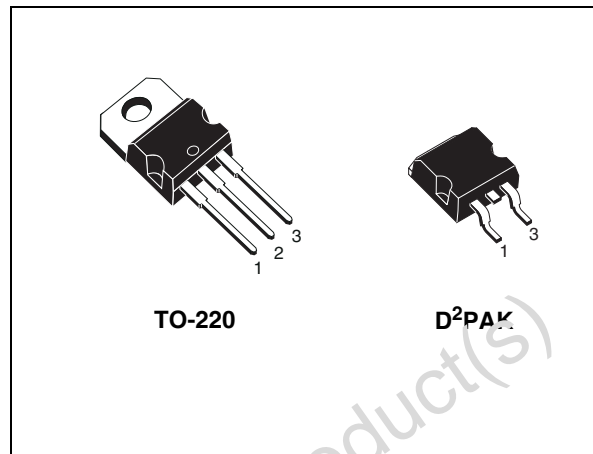


Figure 1. Internal schematic diagram

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB185N10F3	185N10F3	D <sup>2</sup> PAK	Tape and reel
STP185N10F3	185N10F3	TO-220	Tube

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Obsolete Product(s) - Obsolete Product(s)

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS}=0$ )	100	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C=100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2.0	W/ $^\circ\text{C}$
dv/dt	Peak diode recovery voltage slope	TBD	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	TBD	mJ
$T_j$ $T_{stg}$	Operating junction temperature storage temperature	-55 To 175	$^\circ\text{C}$

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting  $T_j=25^\circ\text{C}$ ,  $I_D=60\text{ A}$ ,  $V_{DD}=40\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	TO-220	D <sup>2</sup> PAK	Unit
Rthj-case	Thermal resistance junction-case	0.5		$^\circ\text{C}/\text{W}$
Rthj-a	Thermal resistance junction-ambient max	62.5	--	$^\circ\text{C}/\text{W}$
Rthj-pcb <sup>(1)</sup>	Thermal resistance junction-ambient max	--	35	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	--	$^\circ\text{C}$

1. When mounted on FR-4 board, on 1inch<sup>2</sup>, 2oz Cu.

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max rating},$ $V_{DS} = \text{max rating}, @ 125^{\circ}C$			10 100	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 V$			$\pm 200$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 60 A$ D <sup>2</sup> PAK TO-220			4.5 4.8	m $\Omega$ m $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25 V, f = 1 \text{ MHz},$ $V_{GS} = 0$		TBD		pF
$C_{oss}$	Output capacitance			TBD		pF
$C_{rss}$	Reverse transfer capacitance			TBD		pF
$Q_g$	Total gate charge	$V_{DD} = 80 V, I_D = 120 A,$		100	TBD	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10 V$		TBD		nC
$Q_{gd}$	Gate-drain charge	(see <a href="#">Figure 3</a> )		TBD		nC

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50 V, I_D = 60 A$ $R_G = 4.7 \Omega, V_{GS} = 10 V$ (see <a href="#">Figure 2</a> , <a href="#">Figure 7</a> )		TBD		ns
$t_r$	Rise time			TBD		ns
$t_{d(off)}$	Turn-off delay time			TBD		ns
$t_f$	Fall time			TBD		ns

Table 7. Source drain diode

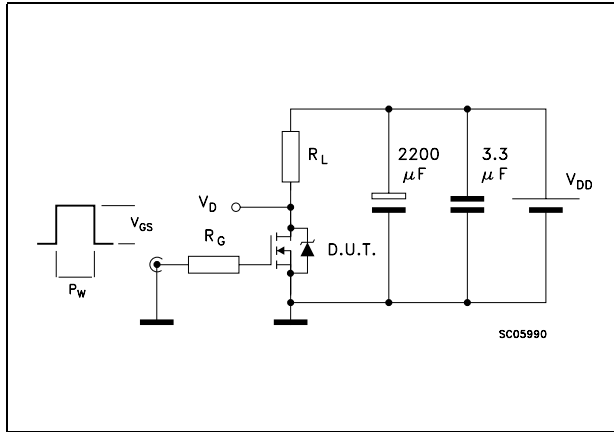
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				120 480	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=120\text{ A}$ , $V_{GS}=0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=120\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=30\text{ V}$ , $T_j=150^\circ\text{C}$ (see <a href="#">Figure 4</a> )		TBD TBD TBD		ns $\mu\text{C}$ A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

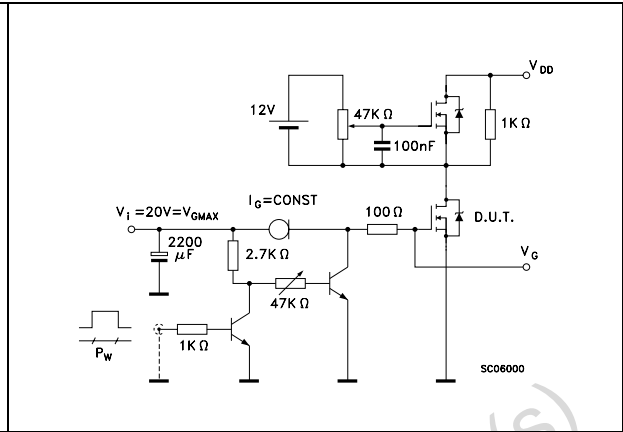
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### 3 Test circuit

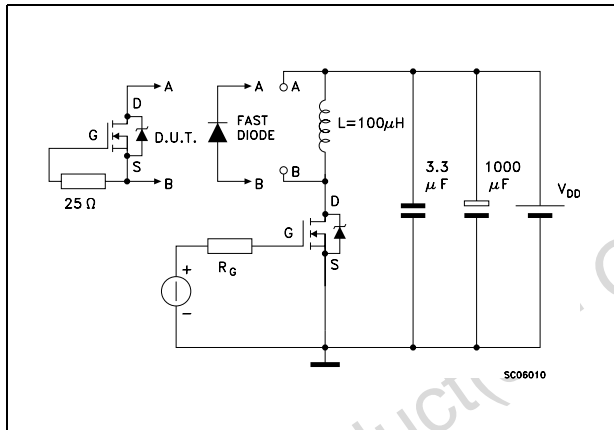
**Figure 2. Switching times test circuit for resistive load**



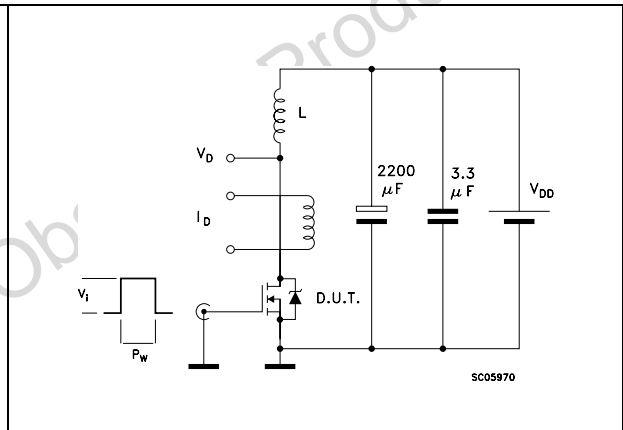
**Figure 3. Gate charge test circuit**



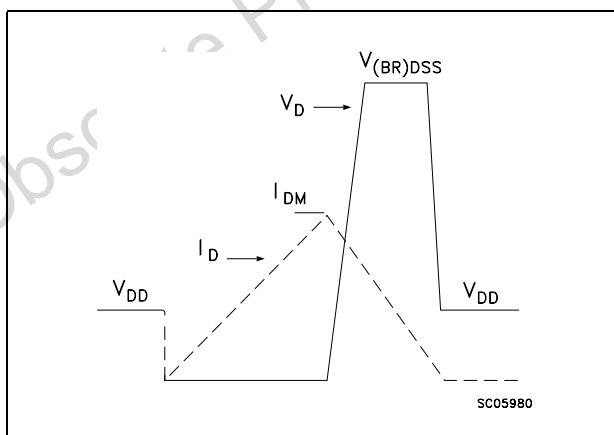
**Figure 4. Test circuit for inductive load switching and diode recovery times**



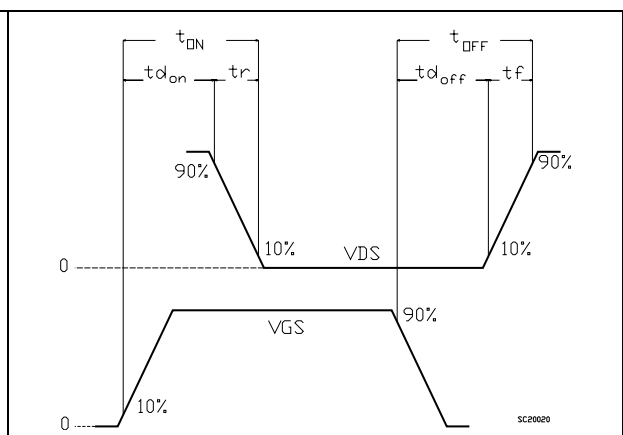
**Figure 5. Unclamped inductive load test circuit**



**Figure 6. Unclamped inductive waveform**



**Figure 7. Switching time waveform**



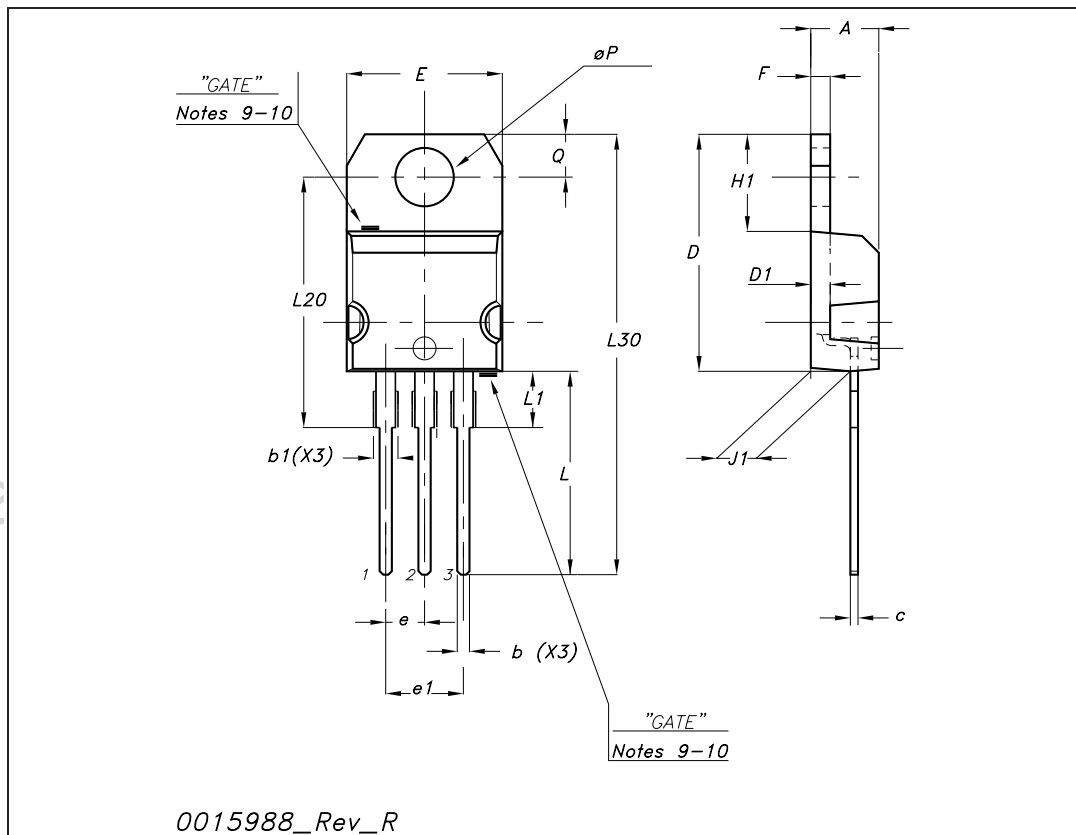
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

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TO-220 mechanical data

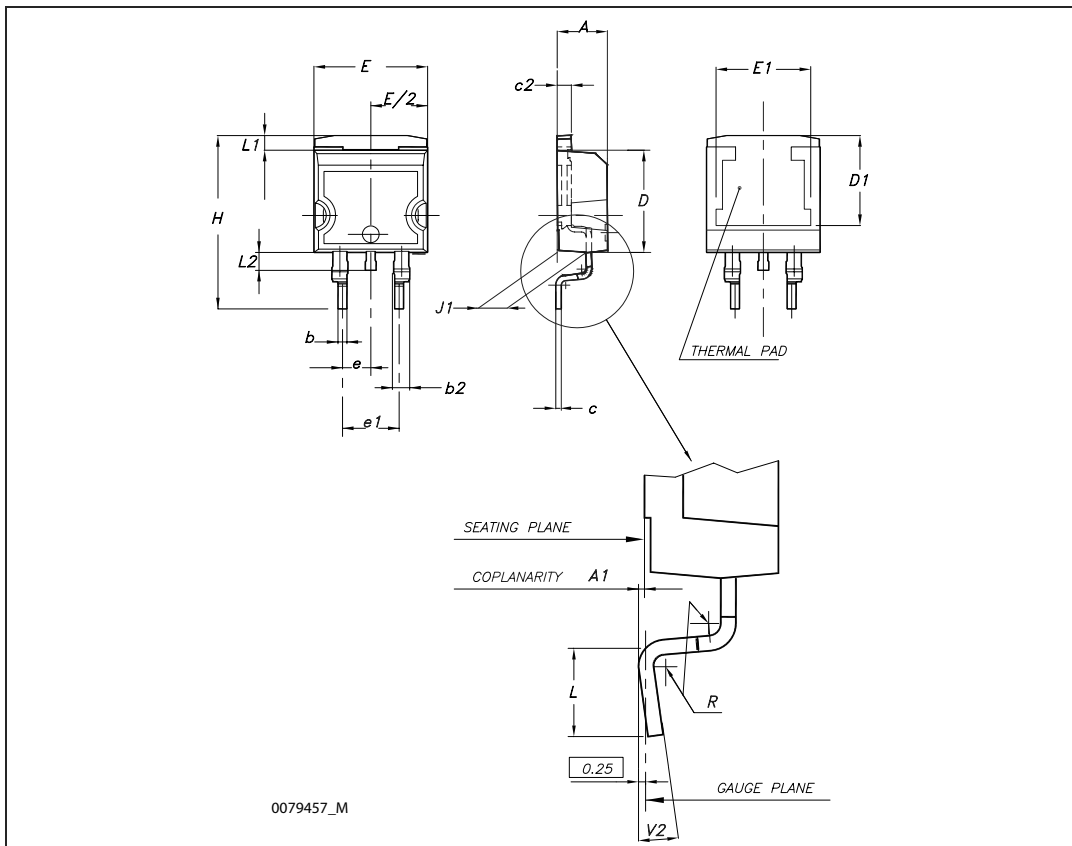
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116





D<sup>2</sup>PAK (TO-263) mechanical data

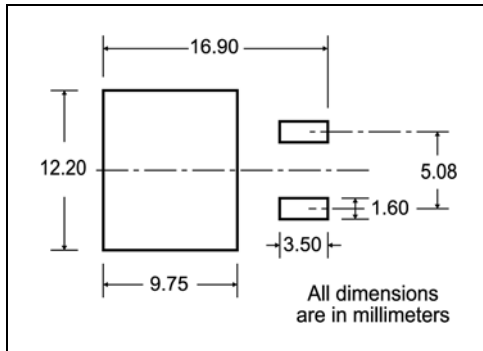
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



Obsolete

# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

\* on sales type

## 6 Revision history

Table 8. Document revision history

Date	Revision	Changes
01-Aug-2007	1	First version

Obsolete Product(s) - Obsolete Product(s)

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